MaxPower Semiconductor

MXP4004AT Datasheet

40V N-Channel MOSFET

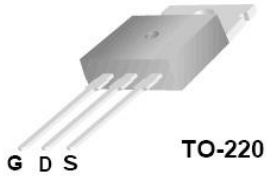
Applications:

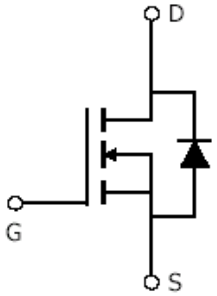
- **Power Supply**
- **DC-DC Converters**

V_{DSS}	$R_{DS(ON)}$ (Max)	I_D[a]
40 V	4.0 mΩ	158 A

Features:

- **LeadFree**
- **Low $R_{DS(ON)}$ to Minimize Conductive Loss**
- **Low Gate Change for Fast Switching Application**
- **Optimized B_{VDSS} Capability**





Ordering Information

Part Number	Package	Brand
MXP4004AT	TO220	MXP

Absolute Maximum Ratings

T_c=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	40	V
I_D[a]	Continuous Drain Current (T_C=25℃)	158	A
E_{AS}	Single Pulse Avalanche Energy (L=11.9mH)	960	mJ
I_{AS}	Pulsed Avalanche Energy	Figure.9	A
T_J and T_{STG}	Operating Junction and Storage Temperature Range	-55 to 175	℃

a. Calculated continuous current based upon maximum allowable junction temperature, +175℃. Package limitation current is 80A.

OFF Characteristics

T_J=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	40			V	V_{GS}=0V, I_D=250μA
I_{DSS}	Drain-to-Source Leakage Current			1	μA	V_{DS}=32V, V_{GS}=0V
				100		V_{DS}=32V, V_{GS}=0V T_J=125 ℃
I_{GSS}	Gate-to-Source Forward Leakage			100	nA	V_{GS}=+20V
	Gate-to-Source Reverse Leakage			100		V_{GS}= -20V

ON Characteristics

T_J=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance			4	mΩ	V_{GS}= 10V, I_D=24A
$V_{GS(TH)}$	Gate Threshold Voltage	2		4	V	V_{DS}=V_{GS}, I_D=250μA

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
C_{iss}	Input Capacitance		3803		pF	V_{GS}=0V, V_{DS}=20V, f=1.0MHz
C_{oss}	Output Capacitance		798			
C_{rss}	Reverse Transfer Capacitance		296			
Q_g	Total Gate Charge		61		nC	V_{DD}=20V, I_D=79A, V_G=10V
Q_{gs}	Gate-to-Source Charge		22			
Q_{gd}	Gate-to-Drain (“Miller”) Charge		24			
$t_{d(on)}$	Turn-on Delay Time		18		ns	V_{DD}=20V, I_D=79A, V_G=10V, R_G=4.7Ω
t_r	Rise Time		63			
$t_{d(off)}$	Turn-off Delay Time		36			
t_f	Fall Time		24			

Source-Drain Diode Characteristics

Tc=25℃ unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
V_{SD}	Diode Forward Voltage			1.2	V	I_S=24A, V_{GS}=0V
Trr	Reverse Recovery Time			39	ns	IS=10A, di/dt = 100A/μs
Qrr	Reverse Recovery Charge			43	nC	

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Figure 1. Maximum Power Dissipation V.S Case Temperature

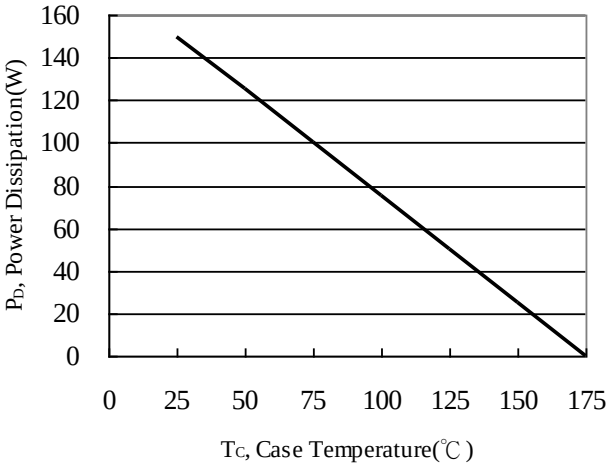


Figure 2. Maximum Continuous Drain Current V.S Case Temperature

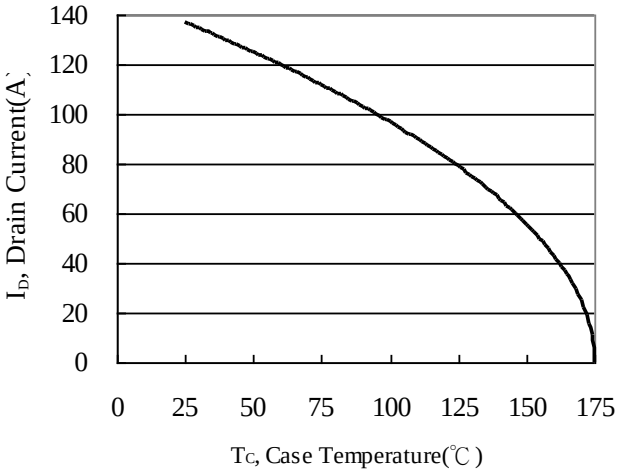


Figure 3. Typical Output Characteristics

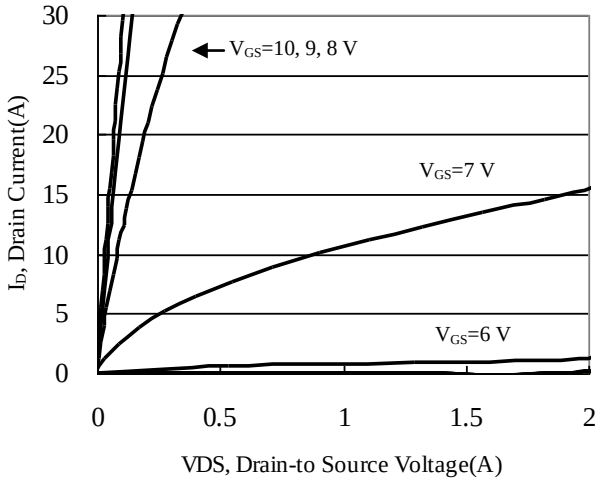


Figure 4. Breakdown Voltage V.S Junction Temperature

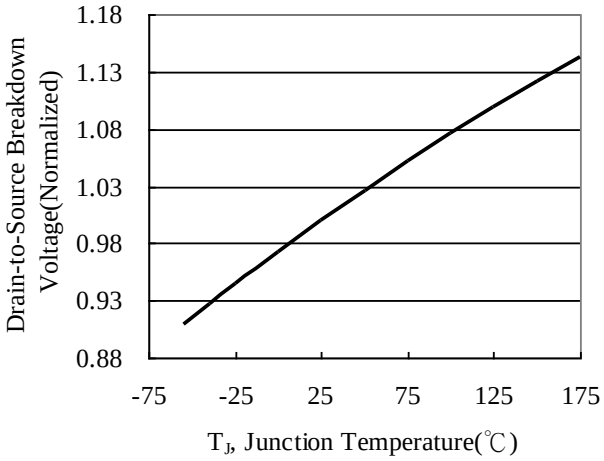


Figure 5. Threshold Voltage V.S Junction Temperature

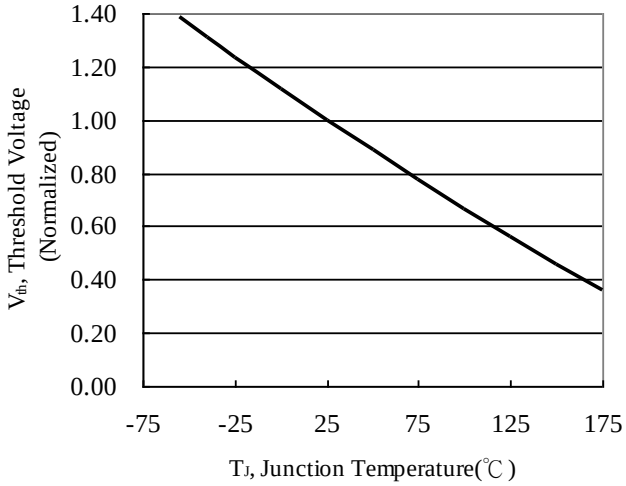


Figure 6. Drain-to-Source Resistance V.S Junction Temperature

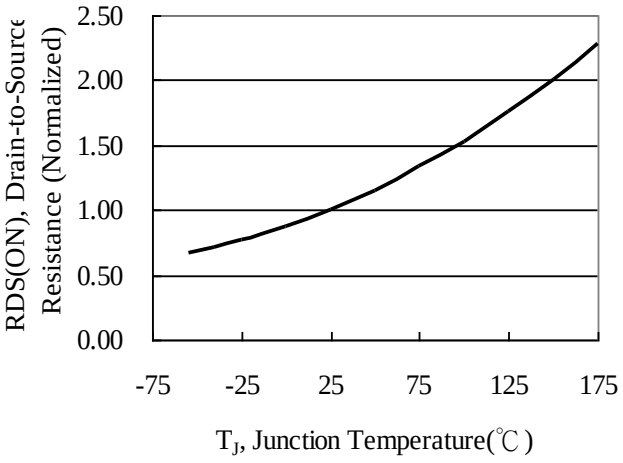


Figure 7. Typical Gate Charge vs. Gate-to-Source Voltage

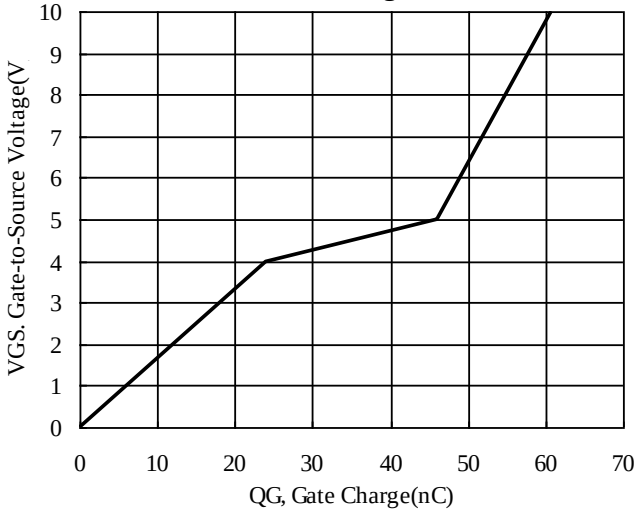


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

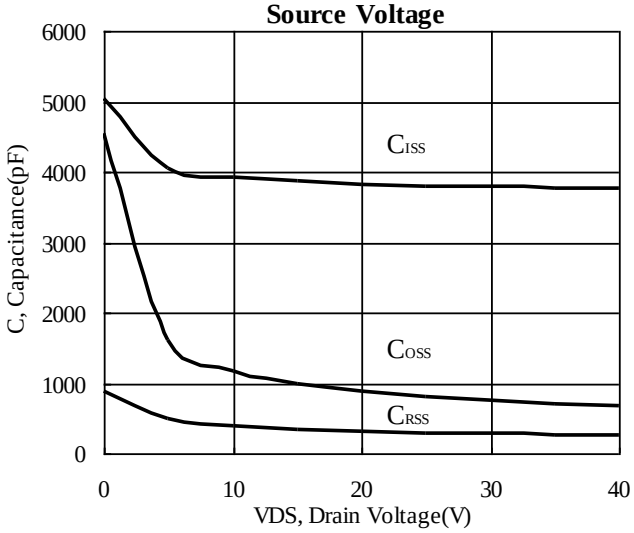


Figure 9. Unclamped Inductive Switching Capability

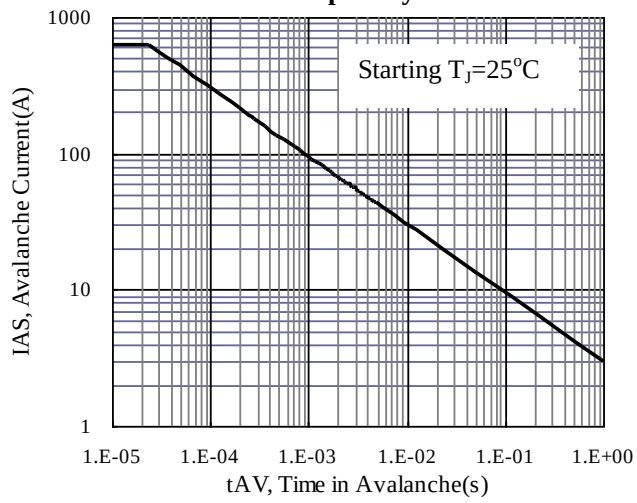
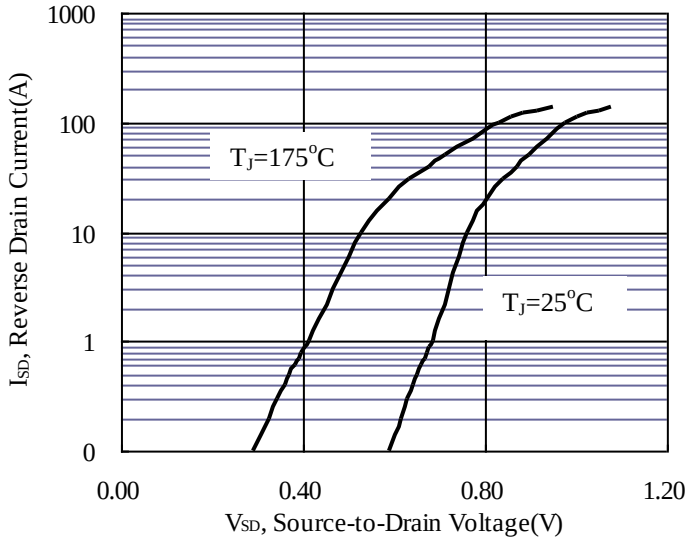


Figure 10. Source-Drain Diode Forward Voltage



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